HEXFRED®
Ultrafast Soft Recovery Diode, 220 A

SOT-227

FEATURES

- Fast recovery time characteristic
- Electrically isolated base plate
- Large creepage distance between terminal
- Simplified mechanical designs, rapid assembly
- Designed and qualified for industrial level
- UL approved file E78996
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Pb-free

RoHS COMPLIANT

PRIMARY CHARACTERISTICS	
V_R	1200 V
V_F (typical)	2.68 V
t_{rr} (typical)	58 ns
$I_{F(AV)}$ per module at T_C	220 A at 38 °C
Package	SOT-227

DESCRIPTION / APPLICATIONS

The dual diode series configuration (VS-HFA220FA120) is used for output rectification or freewheeling/clamping operation and high voltage application.
The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.
These modules are intended for general applications such as HV power supplies, electronic welders, motor control and inverters.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MAX.**	**UNITS**
Cathode to anode voltage	V_R		1200	V
Continuous forward current	I_F	T_C = 68 °C	110	A
Single pulse forward current	I_{FSM}	T_J = 25 °C	700	
Maximum power dissipation per leg	P_D	T_C = 25 °C	500	W
		T_C = 100 °C	400	
RMS isolation voltage	V_{ISOL}	Any terminal to case, t = 1 minute	2500	V
Operating junction and storage temperature range	T_J, T_{Stg}		-55 to +150	°C

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Cathode to anode breakdown voltage	V_{BR}	I_R = 100 µA	1200	-	-	V
Forward voltage	V_{FM}	I_F = 100 A	-	2.68	3.60	
		I_F = 200 A	-	3.41	4.70	
		I_F = 100 A, T_J = 150 °C	-	2.62	2.89	
		I_F = 200 A, T_J = 150 °C	-	3.59	3.89	
Reverse leakage current	I_{RM}	V_R = V_R rated	-	10	75	µA
		T_J = 125 °C, V_R = V_R rated	-	2	-	mA
		T_J = 150 °C, V_R = V_R rated	-	6	15	

DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNITS**
Reverse recovery time	t_{rr}	I_F = 1 A; dI_F/dt = - 200 A/µs; V_R = 30 V		-	58	-	ns
		T_J = 25 °C	I_F = 50 A dI_F/dt = - 200 A/µs V_R = 200 V	-	157	-	
		T_J = 125 °C		-	255	-	
Peak recovery current	I_{RRM}	T_J = 25 °C		-	15	-	A
		T_J = 125 °C		-	22.5	-	
Reverse recovery charge	Q_{rr}	T_J = 25 °C		-	1150	-	nC
		T_J = 125 °C		-	2850	-	
Junction capacitance	C_T	V_R = 1200 V		-	53	-	pF

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Junction to case, single leg conducting	R_{thJC}		-	-	0.25	°C/W
Junction to case, both legs conducting			-	-	0.125	
Case to heatsink	R_{thCS}	Flat, greased surface	-	0.10	-	
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Case style			SOT-227			

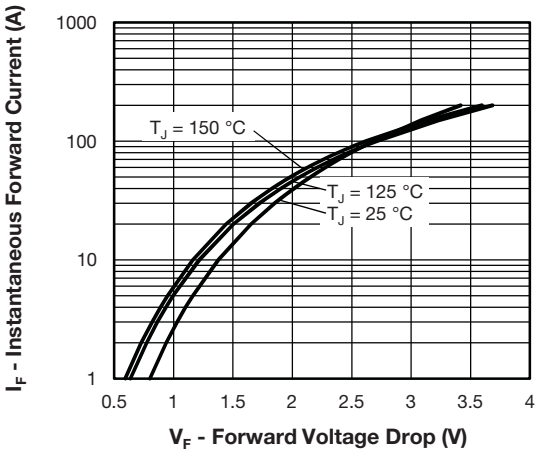


Fig. 1 - Typical Forward Voltage Drop Characteristics (Per Leg)

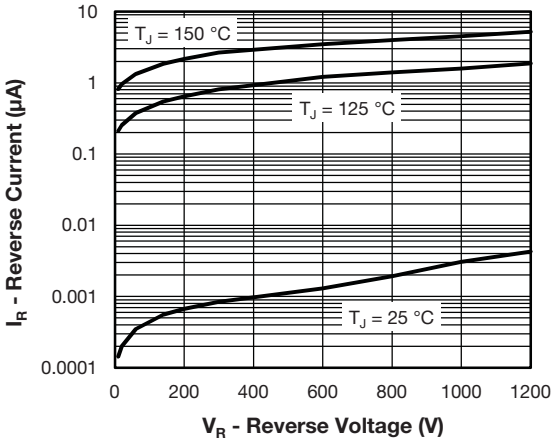


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

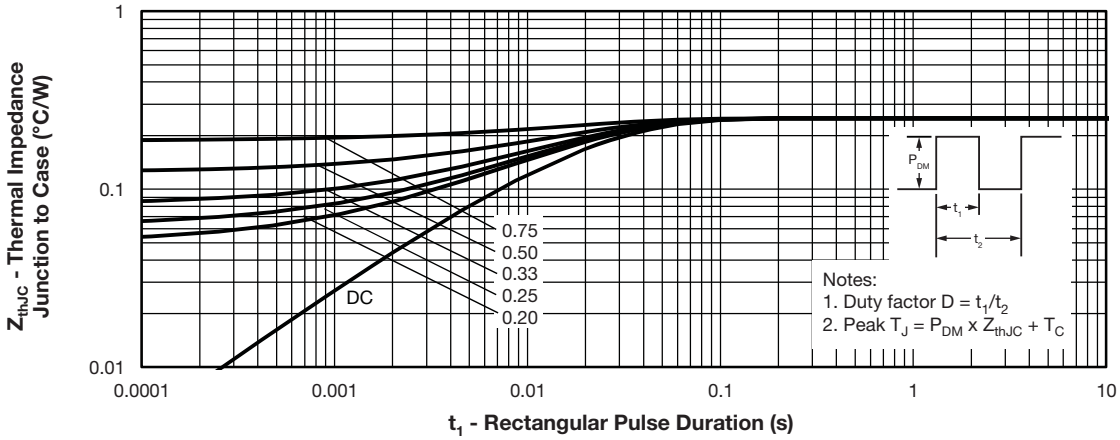


Fig. 3 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

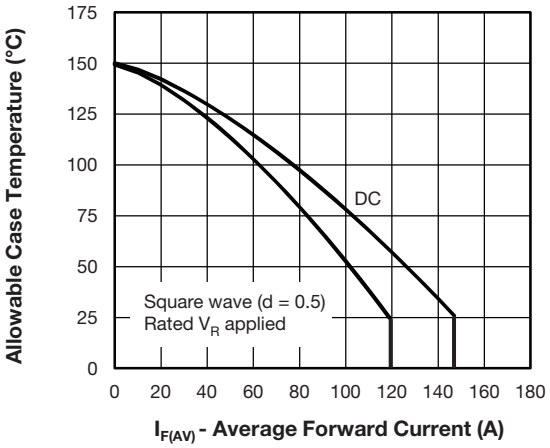


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Leg)

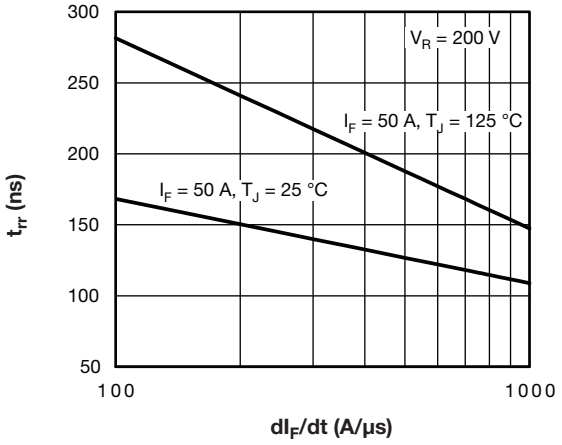


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt

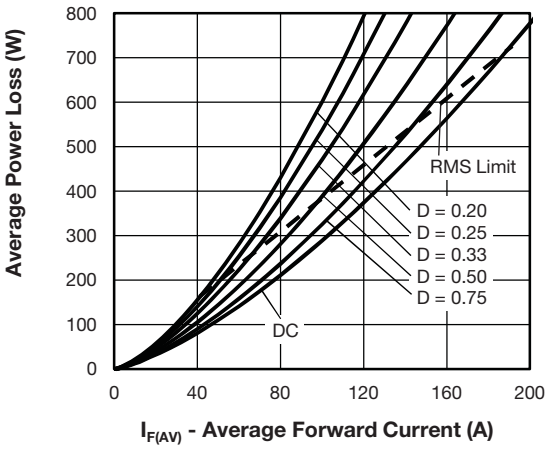


Fig. 5 - Forward Power Losses Characteristics (Per Leg)

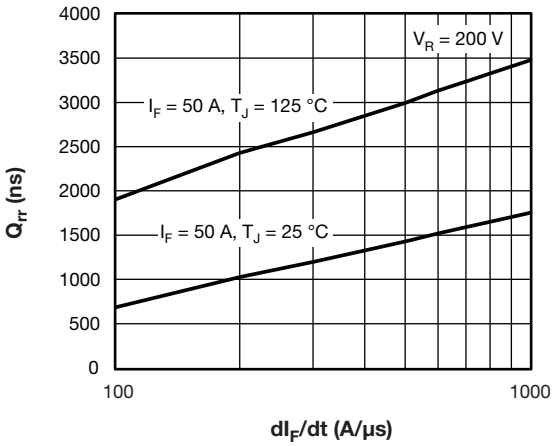


Fig. 7 - Typical Stored Charge vs. dI_F/dt

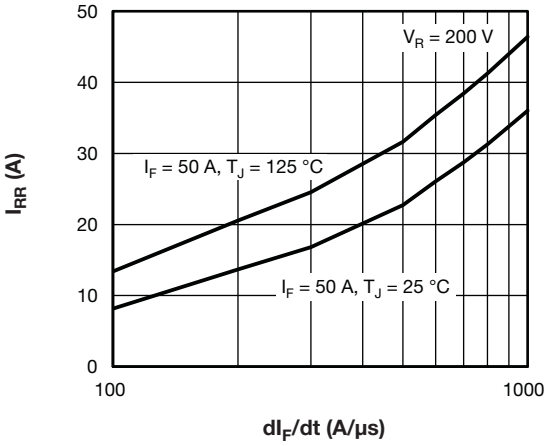


Fig. 8 - Typical Peak Recovery Current vs. dI_F/dt

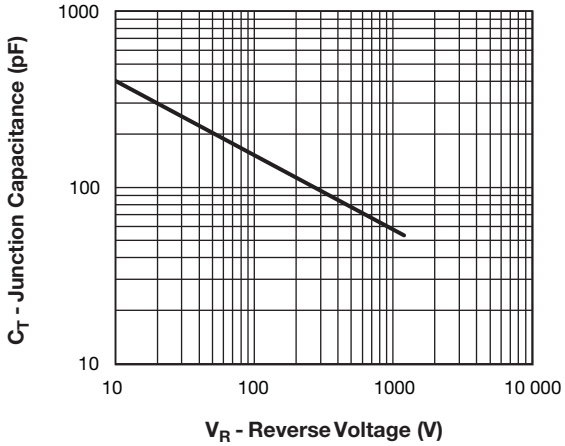


Fig. 9 - Typical Junction Capacitance vs. Reverse Voltage

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;
Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}$/D) (see fig. 5);
Pd_{REV} = inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = rated V_R

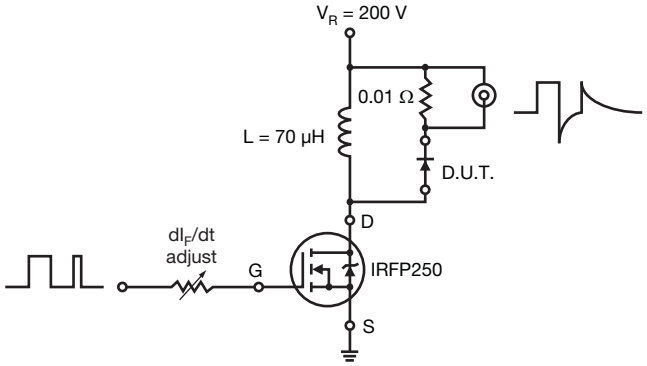
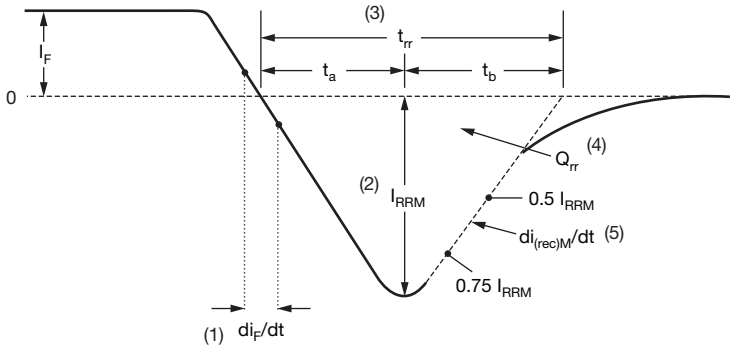


Fig. 10 - Reverse Recovery Parameter Test Circuit



(1) di_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions

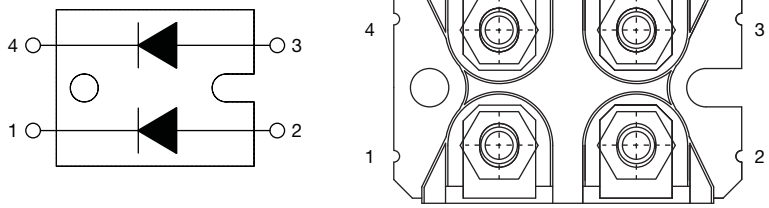
ORDERING INFORMATION TABLE

Device code

VS-	HF	A	220	F	A	120
1	2	3	4	5	6	7

- 1 - Vishay Semiconductors product
- 2 - HEXFRED® family
- 3 - Process designator (A = electron irradiated)
- 4 - Average current (220 = 220 A)
- 5 - Circuit configuration (two separate diodes, parallel pin-out)
- 6 - Package indicator (SOT-227 standard insulated base)
- 7 - Voltage rating (120 = 1200 V)

CIRCUIT CONFIGURATION

CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Two separate diodes, parallel pin-out	F	

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95423
Packaging information	www.vishay.com/doc?95425

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